

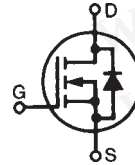
# High Voltage Power MOSFET

**IXTH 6N120**  
**IXTT 6N120**

$$\begin{aligned} V_{DSS} &= 1200 \text{ V} \\ I_{D25} &= 6 \text{ A} \\ R_{DS(on)} &= 2.6 \Omega \end{aligned}$$

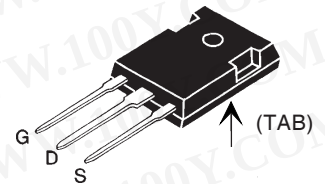
N-Channel Enhancement Mode  
Avalanche Rated

Preliminary Data Sheet

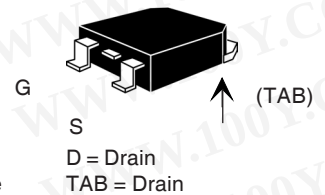


| Symbol    | Test Conditions                                                                                                                         | Maximum Ratings |                  |
|-----------|-----------------------------------------------------------------------------------------------------------------------------------------|-----------------|------------------|
| $V_{DSS}$ | $T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$                                                                                         | 1200            | V                |
| $V_{DGR}$ | $T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ ; $R_{GS} = 1 \text{ M}\Omega$                                                          | 1200            | V                |
| $V_{GS}$  | Continuous                                                                                                                              | $\pm 20$        | V                |
| $V_{GSM}$ | Transient                                                                                                                               | $\pm 30$        | V                |
| $I_{D25}$ | $T_C = 25^\circ\text{C}$                                                                                                                | 6               | A                |
| $I_{DM}$  | $T_C = 25^\circ\text{C}$ , pulse width limited by $T_{JM}$                                                                              | 24              | A                |
| $I_{AR}$  | $T_C = 25^\circ\text{C}$                                                                                                                | 6               | A                |
| $E_{AR}$  | $T_C = 25^\circ\text{C}$                                                                                                                | 25              | mJ               |
| $E_{AS}$  | $T_C = 25^\circ\text{C}$                                                                                                                | 500             | mJ               |
| $dv/dt$   | $I_S \leq I_{DM}$ , $di/dt \leq 100 \text{ A}/\mu\text{s}$ , $V_{DD} \leq V_{DSS}$ ,<br>$T_J \leq 150^\circ\text{C}$ , $R_G = 2 \Omega$ | 5               | V/ns             |
| $P_D$     | $T_C = 25^\circ\text{C}$                                                                                                                | 300             | W                |
| $T_J$     |                                                                                                                                         | -55 ... +150    | $^\circ\text{C}$ |
| $T_{JM}$  |                                                                                                                                         | 150             | $^\circ\text{C}$ |
| $T_{stg}$ |                                                                                                                                         | -55 ... +150    | $^\circ\text{C}$ |
| $T_L$     | 1.6 mm (0.062 in.) from case for 10 s                                                                                                   | 300             | $^\circ\text{C}$ |
| $M_d$     | Mounting torque                                                                                                                         | 1.13/10         | Nm/lb.in.        |
| Weight    | TO-247 AD                                                                                                                               | 6               | g                |
|           | TO-268                                                                                                                                  | 4               | g                |

TO-247 AD (IXTH)



TO-268 (IXTT) Case Style



## Features

- International standard packages
- Low  $R_{DS(on)}$  HDMOS™ process
- Rugged polysilicon gate cell structure
- Unclamped Inductive Switching (UIS) rated
- Low package inductance  
- easy to drive and to protect

## Advantages

- Easy to mount
- Space savings
- High power density

| Symbol       | Test Conditions<br>( $T_J = 25^\circ\text{C}$ , unless otherwise specified)                                     | Characteristic Values |      |                      |
|--------------|-----------------------------------------------------------------------------------------------------------------|-----------------------|------|----------------------|
|              |                                                                                                                 | Min.                  | Typ. | Max.                 |
| $V_{DSS}$    | $V_{GS} = 0 \text{ V}$ , $I_D = 250 \mu\text{A}$                                                                | 1200                  |      | V                    |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}$ , $I_D = 250 \mu\text{A}$                                                                     | 2.5                   |      | V                    |
| $I_{GSS}$    | $V_{GS} = \pm 20 \text{ V}_{DC}$ , $V_{DS} = 0$                                                                 |                       |      | $\pm 100 \text{ nA}$ |
| $I_{DSS}$    | $V_{DS} = V_{DSS}$<br>$V_{GS} = 0 \text{ V}$                                                                    |                       |      | 25 $\mu\text{A}$     |
|              |                                                                                                                 |                       |      | 500 $\mu\text{A}$    |
| $R_{DS(on)}$ | $V_{GS} = 10 \text{ V}$ , $I_D = 0.5 I_{D25}$<br>Pulse test, $t \leq 300 \mu\text{s}$ , duty cycle $d \leq 2\%$ |                       |      | 2.6 $\Omega$         |

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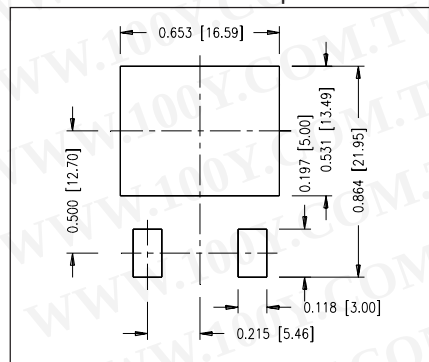
| Symbol       | Test Conditions                                                                                   | Characteristic Values<br>( $T_J = 25^\circ\text{C}$ , unless otherwise specified) |      |      |
|--------------|---------------------------------------------------------------------------------------------------|-----------------------------------------------------------------------------------|------|------|
|              |                                                                                                   | Min.                                                                              | Typ. | Max. |
| $g_{fs}$     | $V_{DS} = 20\text{ V}; I_D = 0.5 I_{D25}$ , pulse test                                            | 3                                                                                 | 5    | S    |
| $C_{iss}$    | $V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$                                     | 1950                                                                              | 175  | pF   |
| $C_{oss}$    |                                                                                                   |                                                                                   |      | pF   |
| $C_{rss}$    |                                                                                                   |                                                                                   |      | pF   |
| $t_{d(on)}$  | $V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}$<br>$R_G = 4.7\ \Omega$ (External) | 28                                                                                | 33   | ns   |
| $t_r$        |                                                                                                   |                                                                                   |      | ns   |
| $t_{d(off)}$ |                                                                                                   |                                                                                   |      | ns   |
| $t_f$        |                                                                                                   |                                                                                   |      | ns   |
| $Q_{g(on)}$  | $V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}$                                   | 56                                                                                | 13   | nC   |
| $Q_{gs}$     |                                                                                                   |                                                                                   |      | nC   |
| $Q_{gd}$     |                                                                                                   |                                                                                   |      | nC   |
| $R_{thJC}$   | (TO-247)                                                                                          | 0.21                                                                              | 0.42 | K/W  |
| $R_{thCK}$   |                                                                                                   |                                                                                   |      | K/W  |

## Source-Drain Diode

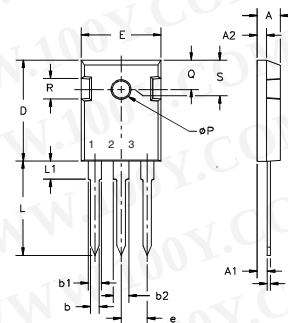
| Symbol   | Test Conditions                                                                                       | Characteristic Values<br>( $T_J = 25^\circ\text{C}$ , unless otherwise specified) |      |       |
|----------|-------------------------------------------------------------------------------------------------------|-----------------------------------------------------------------------------------|------|-------|
|          |                                                                                                       | min.                                                                              | typ. | max.  |
| $I_S$    | $V_{GS} = 0\text{ V}$                                                                                 |                                                                                   |      | 6 A   |
| $I_{SM}$ | Repetitive                                                                                            |                                                                                   |      | 24 A  |
| $V_{SD}$ | $I_F = I_S, V_{GS} = 0\text{ V}$ ,<br>Pulse test, $t \leq 300\ \mu\text{s}$ , duty cycle $d \leq 2\%$ |                                                                                   |      | 1.5 V |
| $T_{rr}$ | $I_F = 6\text{ A}$<br>$-di/dt = 100\text{ A}/\mu\text{s}$                                             |                                                                                   | 850  | ns    |

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## Min Recommended Footprint



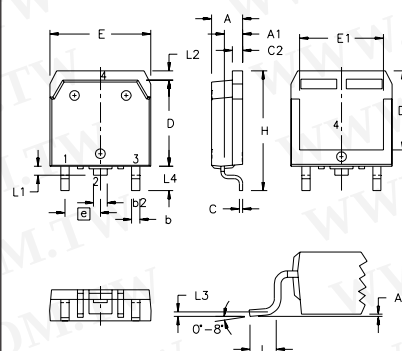
## TO-247 AD Outline



Terminals: 1 - Gate 2 - Drain  
3 - Source Tab - Drain

| Dim.           | Millimeter |       | Inches   |       |
|----------------|------------|-------|----------|-------|
|                | Min.       | Max.  | Min.     | Max.  |
| A              | 4.7        | 5.3   | .185     | .209  |
| A <sub>1</sub> | 2.2        | 2.54  | .087     | .102  |
| A <sub>2</sub> | 2.2        | 2.6   | .059     | .098  |
| b              | 1.0        | 1.4   | .040     | .055  |
| b <sub>1</sub> | 1.65       | 2.13  | .065     | .084  |
| b <sub>2</sub> | 2.87       | 3.12  | .113     | .123  |
| C              | .4         | .8    | .016     | .031  |
| D              | 20.80      | 21.46 | .819     | .845  |
| E              | 15.75      | 16.26 | .610     | .640  |
| e              | 5.20       | 5.72  | 0.205    | 0.225 |
| L              | 19.81      | 20.32 | .780     | .800  |
| L <sub>1</sub> |            | 4.50  |          | .177  |
| ØP             | 3.55       | 3.65  | .140     | .144  |
| Q              | 5.89       | 6.40  | 0.232    | 0.252 |
| R              | 4.32       | 5.49  | .170     | .216  |
| S              | 6.15 BSC   |       | .242 BSC |       |

## TO-268 Outline



Terminals: 1 - Gate 2 - Drain  
3 - Source Tab - Drain

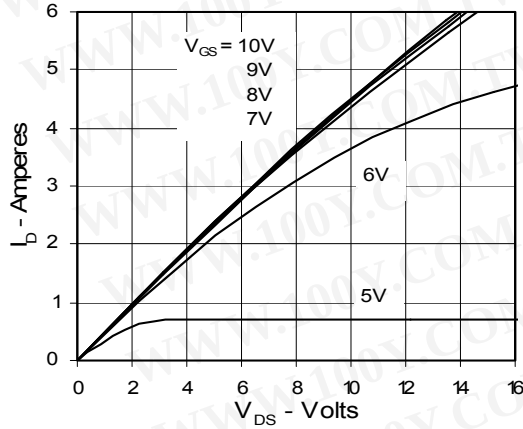
| SYM            | INCHES   |      | MILLIMETERS |       |
|----------------|----------|------|-------------|-------|
|                | MIN      | MAX  | MIN         | MAX   |
| A              | .193     | .201 | 4.90        | 5.10  |
| A <sub>1</sub> | .106     | .114 | 2.70        | 2.90  |
| A <sub>2</sub> | .001     | .010 | 0.02        | 0.25  |
| b              | .045     | .057 | 1.15        | 1.45  |
| b <sub>2</sub> | .075     | .083 | 1.90        | 2.10  |
| C              | .016     | .026 | 0.40        | 0.65  |
| C <sub>2</sub> | .057     | .063 | 1.45        | 1.60  |
| D              | .543     | .551 | 13.80       | 14.00 |
| D <sub>1</sub> | .488     | .500 | 12.40       | 12.70 |
| E              | .624     | .632 | 15.85       | 16.05 |
| E <sub>1</sub> | .524     | .535 | 13.30       | 13.60 |
| e              | .215 BSC |      | 5.45 BSC    |       |
| H              | .736     | .752 | 18.70       | 19.10 |
| L              | .094     | .106 | 2.40        | 2.70  |
| L <sub>1</sub> | .047     | .055 | 1.20        | 1.40  |
| L <sub>2</sub> | .039     | .045 | 1.00        | 1.15  |
| L <sub>3</sub> | .010 BSC |      | 0.25 BSC    |       |
| L <sub>4</sub> | .150     | .161 | 3.80        | 4.10  |

IXYS reserves the right to change limits, test conditions, and dimensions.

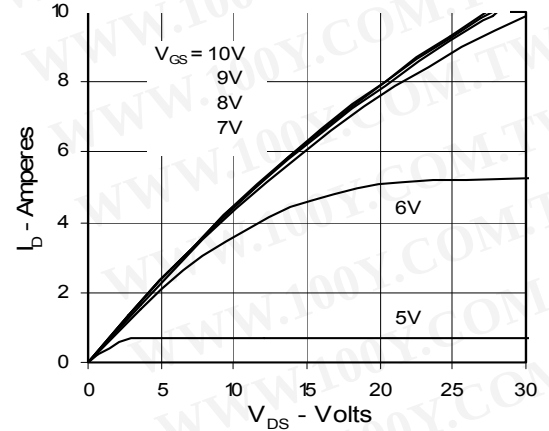
IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715 6,306,728B1 6,259,123B1 6,306,728B1  
 4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025 6,404,065B1 6,162,665 6,534,343

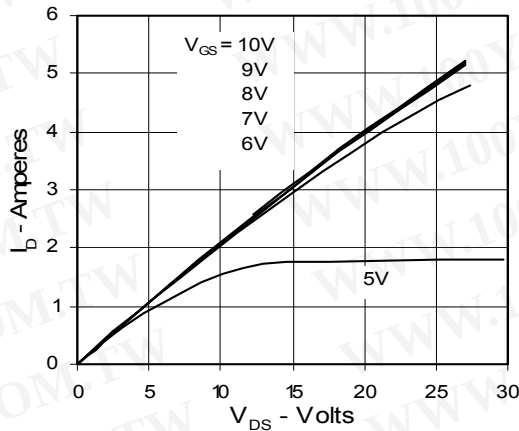
**Fig. 1. Output Characteristics**  
**@ 25 Deg. C**



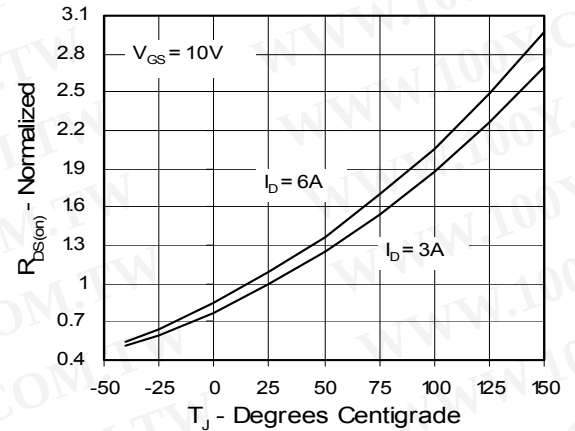
**Fig. 2. Extended Output Characteristics**  
**@ 25 deg. C**



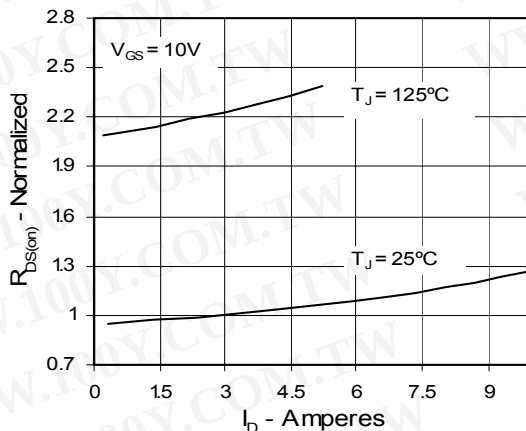
**Fig. 3. Output Characteristics**  
**@ 125 Deg. C**



**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_{D25}$  Value vs. Junction Temperature**



**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_{D25}$  Value vs.  $I_D$**



**Fig. 6. Drain Current vs. Case Temperature**

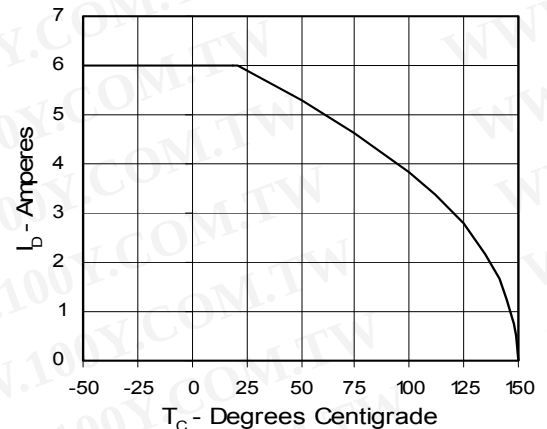


Fig. 7. Input Admittance

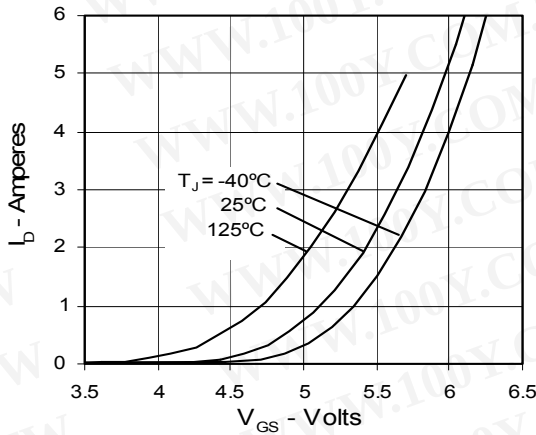


Fig. 8. Transconductance

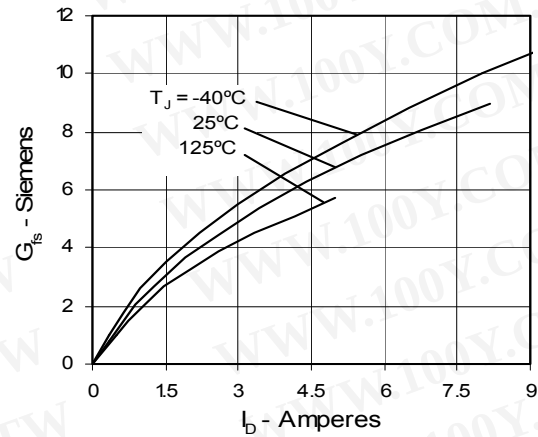


Fig. 9. Source Current vs. Source-To-Drain Voltage

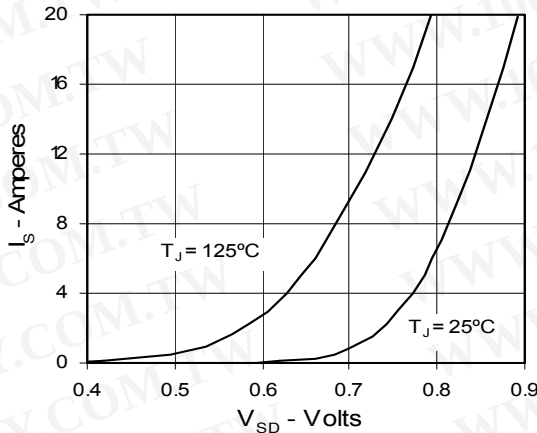


Fig. 10. Gate Charge

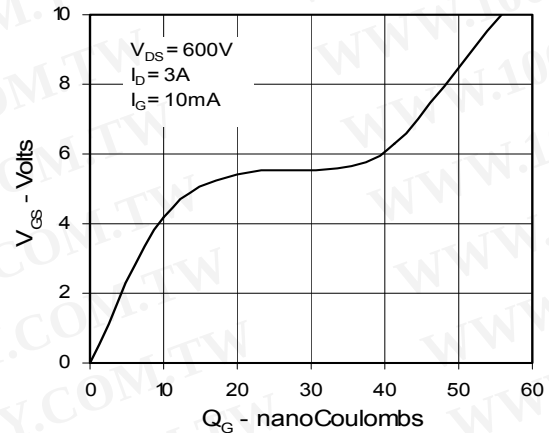


Fig. 11. Capacitance

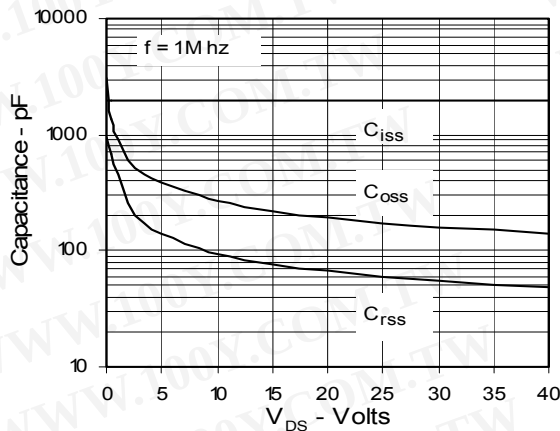


Fig. 12. Maximum Transient Thermal Resistance

